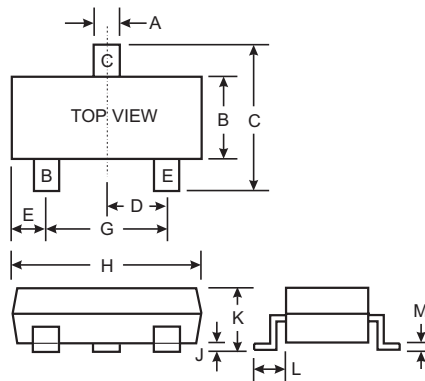


Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (MMBTA13 / MMBTA14)
- Ideal for Medium Power Amplification and Switching
- High Current Gain

Mechanical Data

- Case: SOT-23, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- MMBTA63 Marking: K2E
- MMBTA64 Marking: K3E
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.19	1.40
C	2.10	2.50
D	0.89	1.05
E	0.45	0.61
G	1.78	2.05
H	2.65	3.05
J	0.013	0.15
K	0.89	1.10
L	0.45	0.61
M	0.076	0.178
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	MMBTA63	MMBTA64	Unit
Collector-Base Voltage	V _{CB0}	-30		V
Collector-Emitter Voltage	V _{CEO}	-30		V
Emitter-Base Voltage	V _{EBO}	-10		V
Collector Current - Continuous (Note 1)	I _C	-500		mA
Power Dissipation (Note 1)	P _d	350		mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	357		K/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150		°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-30	—	V	I _C = -100μA, V _{BE} = 0V
Collector Cutoff Current	I _{CB0}	—	-100	nA	V _{CB} = -30V, I _E = 0
Emitter Cutoff Current	I _{EBO}	—	-100	nA	V _{EB} = -10V, I _C = 0
ON CHARACTERISTICS (Note 2)					
DC Current Gain	MMBTA63 MMBTA64 MMBTA63 MMBTA64 h _{FE}	5,000 10,000 10,000 20,000	—	—	I _C = -10mA, V _{CE} = -5.0V I _C = -10mA, V _{CE} = -5.0V I _C = -100mA, V _{CE} = -5.0V I _C = -100mA, V _{CE} = -5.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-1.5	V	I _C = -100mA, I _B = -100μA
Base- Emitter Saturation Voltage	V _{BE(SAT)}	—	-2.0	V	I _C = -100mA, V _{CE} = -5.0V
SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f _T	125	—	MHz	V _{CE} = -5.0V, I _C = -10mA, f = 100MHz

- Notes:
1. Valid provided that terminals are kept at ambient temperature.
 2. Pulse test: Pulse width ≤ 300μs, duty cycle ≤ 2%.